

HIGH-VOLTAGE HIGH-CURRENT DARLINGTON TRANSISTOR ARRAYS

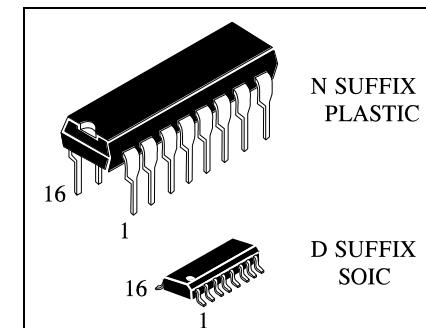
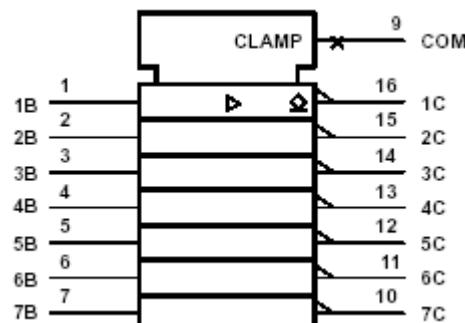
ILN2004

The ILN2004 are monolithic high-voltage, high-current Darlington transistor arrays. Each consists of seven n-p-n Darlington pairs that feature high-voltage outputs with common-cathode clamp diodes for switching inductive loads. The collector-current rating of a single Darlington pair is 500 mA. The Darlington pairs may be paralleled for higher current capability. Applications include relay drivers, hammer drivers, lamp drivers, display drivers (LED and gas discharge), line drivers, and logic buffers.

The ILN2004 has a $10.5\text{k}\Omega$ series base resistor for each Darlington pair for operation directly with 6-15V CMOS devices.

- 500-mA Rated Collector Current (Single Output)
- High-Voltage Outputs . . . 50 V
- Output Clamp Diodes
- Inputs Compatible With Various Types of Logic
- Relay Driver Applications

LOGIC SYMBOL LOGIC DIAGRAM

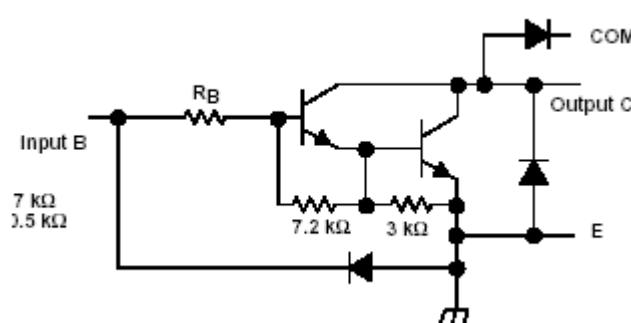
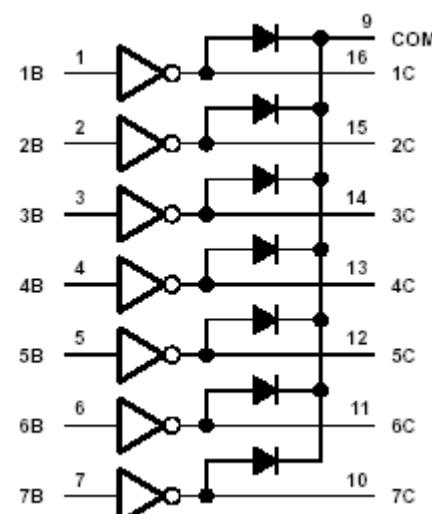


ORDERING INFORMATION

ILN2004N Plastic

ILN2004D SOIC

$T_A = -40^\circ\text{C}$ to 85°C for all packages



SCHEMATICS (each Darlington Pair)

ILN2004: $R_B = 10.5\text{k}\Omega$

All resistor values shown are nominal.

Absolute maximum ratings at 25°C free-air temperature (unless otherwise noted)

Symbol	Parameter	Value	Unit
	Collector-emitter voltage	50	V
V _I	Input voltage(see Note 1)	30	V
	Peak collector current (see Figures 14 and 15)	500	mA
I _{OK}	Output clamp current	500	mA
	Total emitter-terminal current	-2.5	A
	Continuous total power dissipation	See Dissipation Rating Table	
T _A	Operating free-air temperature range	-40 to 85	°C
T _{stg}	Storage temperature range	-55 to 150	°C
	Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260	°C

NOTE 1: All voltage values are with respect to the emitter/substrate terminal E, unless otherwise noted.

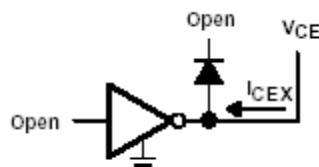
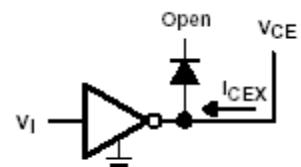
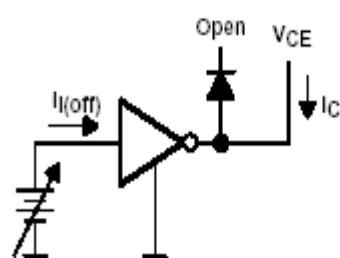
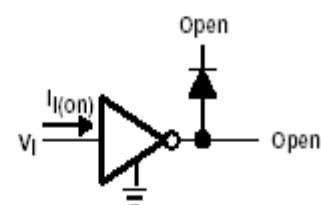
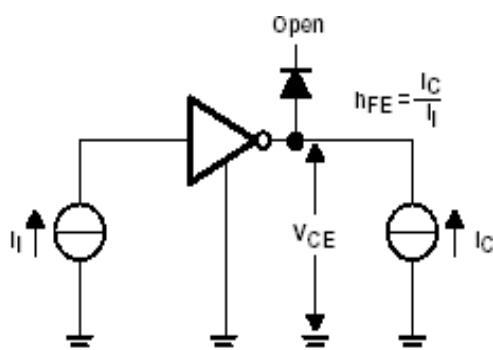
Dissipation Rating Table

PACKAGE	T _A =25°C POWER RATING	DERATING FACTOR above T _A =25°C	T _A =85°C POWER RATING
D	1210mW	7.6mW/°C	494mW
N	1420mW	9.2mW/°C	598 mW

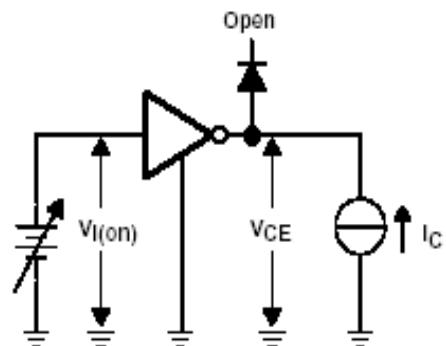
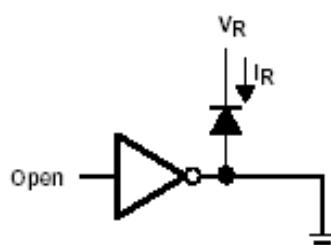
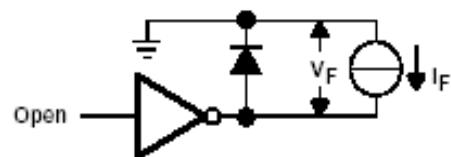
Electrical Characteristics, T_A = 25°C (unless otherwise noted)

Symbol	Parameter	Test Figure	Test Conditions	Min.	Typ.	Max.	Unit
Vi(on)	Input Voltage	6	V _{CE} =2V I _C = 125mA I _C = 200mA I _C = 275mA I _C = 350mA			5 6 7 8	V
V _{CE(sat)}	Collector-emitter Saturation Voltage	5	I _C = 100mA, I _B = 250mA I _C = 200 mA, I _B = 350mA I _C = 350mA, I _B = 500mA		0.9 1.1 1.3	1.1 1.3 1.6	V
I _{CEX}	Output Leakage Current	2	V _{CE} = 50V, V _i = 1V			500	uA
V _F	Clamp Diode Forward Voltage	8	I _F = 350mA		1.7	2	V
I _{i(off)}	Off-state Input Current	3	V _{CE} =50V, T _{amb} = 70°C, I _C = 500mA	50	65		uA
I _i	Input Current	4	V _i = 5V V _i = 12V		0.35 1	0.5 1.45	mA
I _R	Clamp Reverse Current	7	V _R = 50V T _{amb} = 70°C, V _R = 50V			50 100	uA
C _i	Input Capacitance				15	25	pF
Switching Characteristics, T _A =25°C							
t _{PLH}	Turn-on Delay Time		See Fig.9		0.25	1	us
t _{PHL}	Turn-off Delay Time		See Fig.9		0.25	1	us
V _{OH}	High level output voltage after switching		V _S =50V, I _O =300mA See Fig.10	V _S -20			mV

PARAMETER MEASUREMENT INFORMATION

Figure 1. I_{CEx} Test CircuitFigure 2. I_{CEx} Test CircuitFigure 3. $I_{I(off)}$ Test CircuitFigure 4. I_I Test Circuit

NOTE: I_I is fixed for measuring $V_{CE(sat)}$, variable for measuring hFE .

Figure 5. hFE , $V_{CE(sat)}$ Test CircuitFigure 6. $V_{I(on)}$ Test CircuitFigure 7. I_R Test CircuitFigure 8. V_F Test Circuit

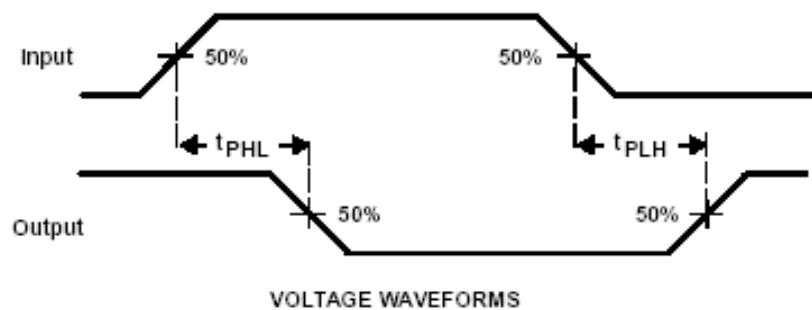
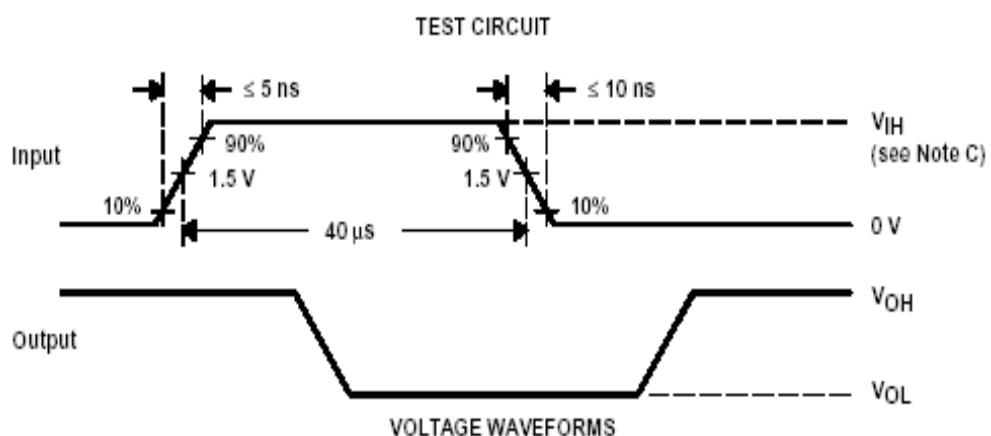


Figure 9. Propagation Delay-Time Waveforms



NOTES: A. The pulse generator has the following characteristics: PRR = 12.5 kHz, $Z_0 = 50 \Omega$.

B. C_L includes probe and jig capacitance.

C. $V_{IH} = 12$ V;

Figure 10. Latch-Up Test Circuit and Voltage Waveforms

TYPICAL CHARACTERISTICS

COLLECTOR-EMITTER SATURATION VOLTAGE vs
COLLECTOR CURRENT (ONE DARLINGTON)

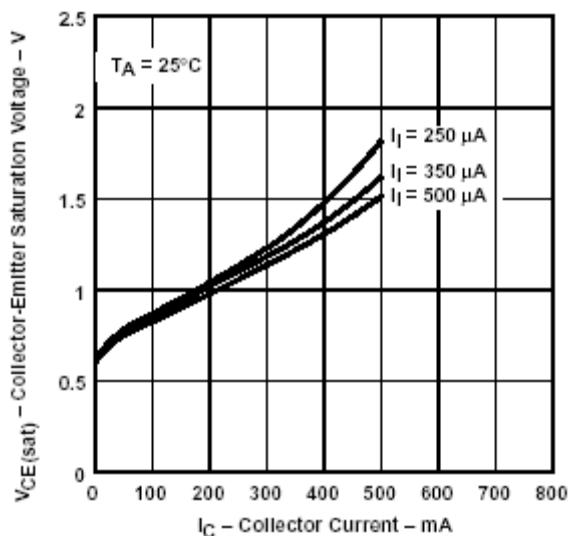


Figure 11

COLLECTOR-EMITTER SATURATION VOLTAGE vs
TOTAL COLLECTOR CURRENT TWO
DARLINGTONS PARALLELED)

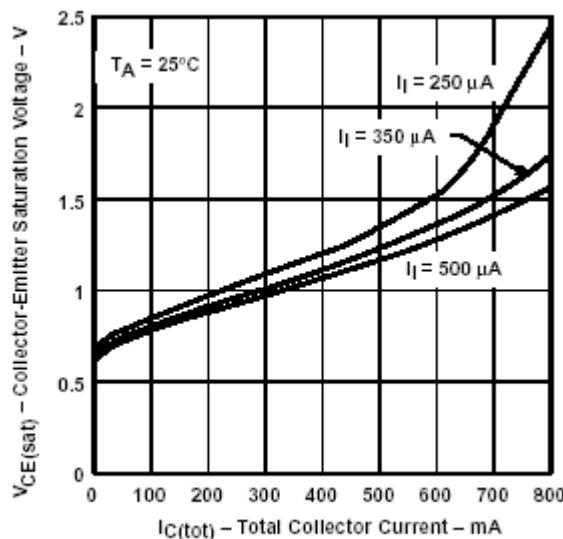


Figure 12

COLLECTOR CURRENT vs INPUT CURRENT

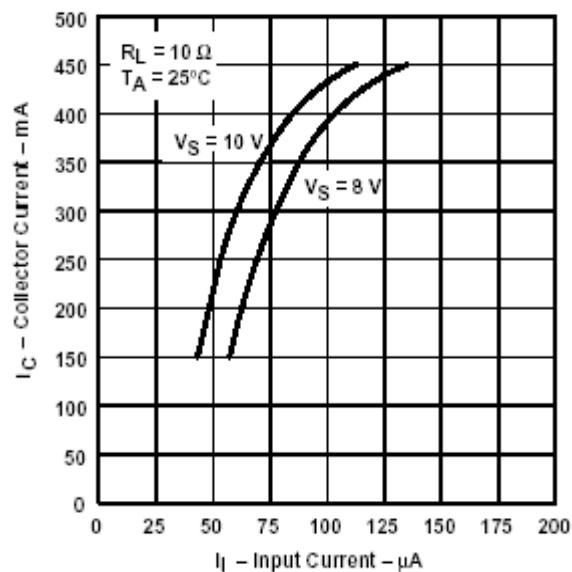


Figure 13

THERMAL INFORMATION

D PACKAGE MAXIMUM COLLECTOR CURRENT
vs DUTY CYCLE

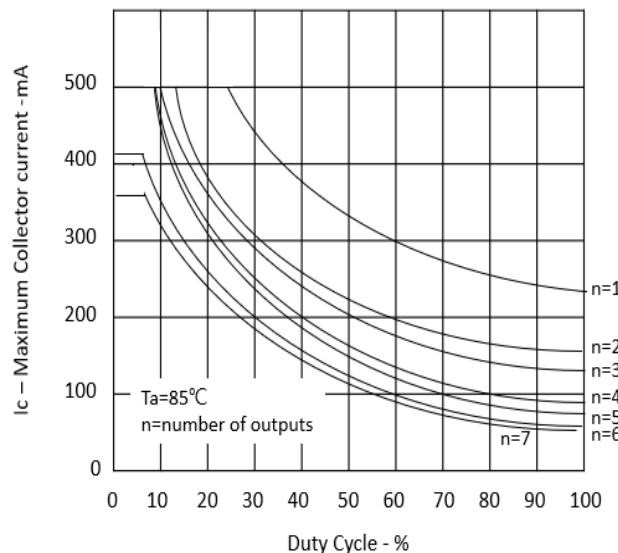


Figure 14

N PACKAGE MAXIMUM COLLECTOR CURRENT
vs DUTY CYCLE

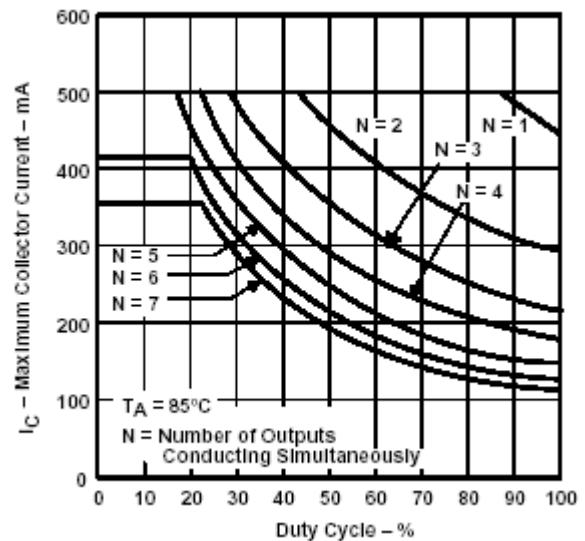


Figure 15

APPLICATION INFORMATION

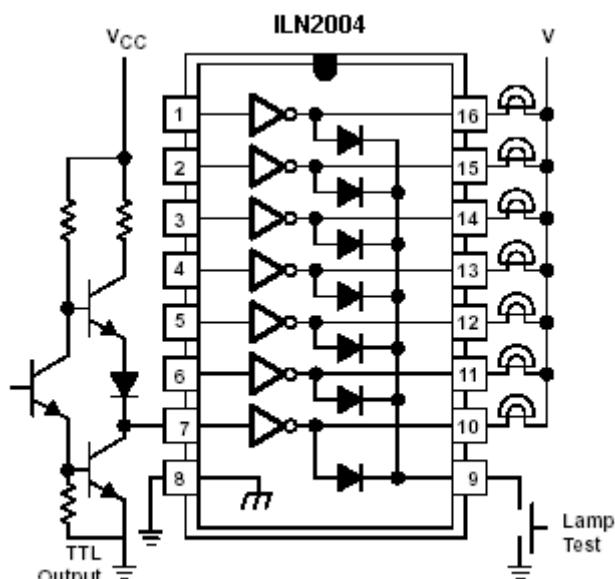


Figure 16. TTL to Load

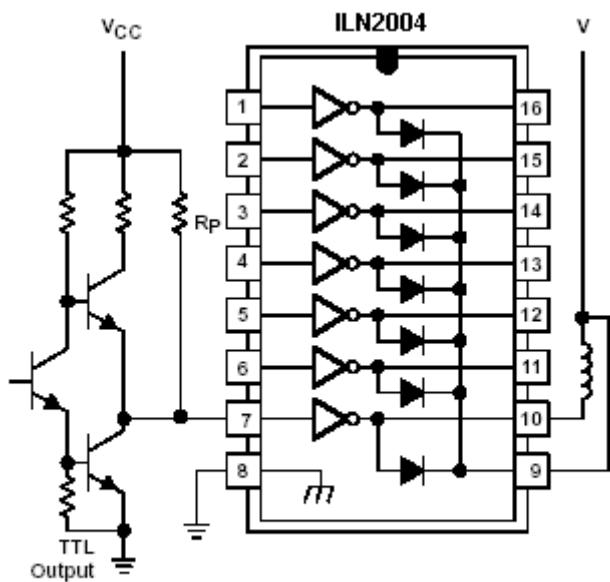
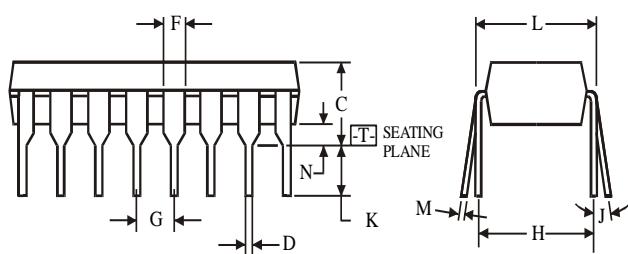
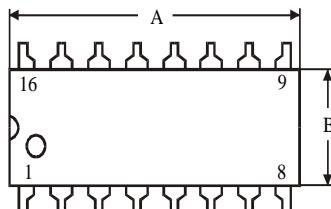


Figure 17. Use of Pullup Resistors to Increase Drive Current

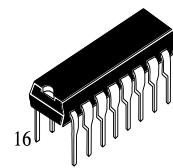
**N SUFFIX PLASTIC DIP
(MS - 001BB)**



NOTES:

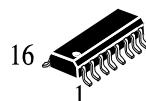
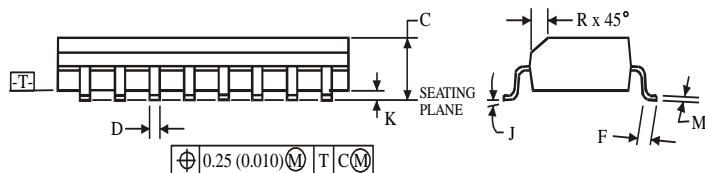
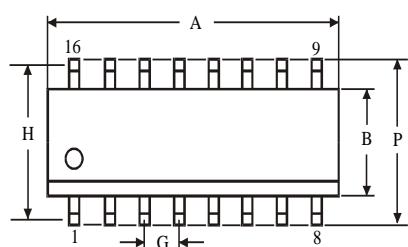
- Dimensions "A", "B" do not include mold flash or protrusions.

Maximum mold flash or protrusion 0.25 mm (0.010) per side.



Symbol	Dimension, mm	
	MIN	MAX
A	18.67	19.69
B	6.10	7.11
C		5.33
D	0.36	0.56
F	1.14	1.78
G		2.54
H		7.62
J	0°	10°
K	2.92	3.81
L	7.62	8.26
M	0.20	0.36
N	0.38	

**D SUFFIX SOIC
(MS - 012AC)**



Symbol	Dimension, mm	
	MIN	MAX
A	9.80	10.00
B	3.80	4.00
C	1.35	1.75
D	0.33	0.51
F	0.40	1.27
G		1.27
H		5.72
J	0°	8°
K	0.10	0.25
M	0.19	0.25
P	5.80	6.20
R	0.25	0.50

NOTES:

- Dimensions A and B do not include mold flash or protrusion.
- Maximum mold flash or protrusion 0.15 mm (0.006) per side for A; for B - 0.25 mm (0.010) per side.

Type Document Revision History

Rev	Date	Initiator	Description of Change
00	Jan. 2011	SM Jung	Establishment
01	Oct. 2018	HG Ryu	Changed the Temperature Range Operation Temperature: -20°C to 85° C -> -40°C to 85° C Storage temperature range: -60°C to 150° C -> -55°C to 150° C
02	Jun. 2019	H I Kim	Correction graph and figures